

10A Avg.

40 Volts

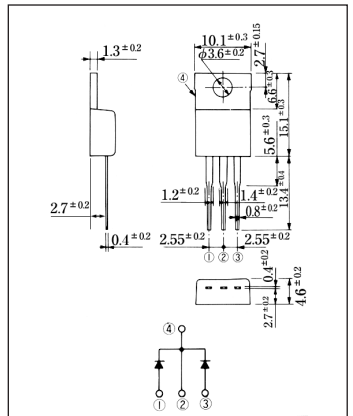
SBD

GCQ10A04

最大定格 Maximum Ratings

Item	Symbol	Conditions	Unit	
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	$V_{RRM}$	40	V	
非くり返しピーク逆電圧 Non-repetitive Peak Reverse Voltage	$V_{RSM}$	45	V	
平均整流電流 Average Rectified Forward Current	$I_O$	50Hz, 正弦全波通電抵抗負荷 50Hz Full Sine Wave Resistive Load	$T_c=116^\circ\text{C}$ 10	A
実効順電流 R.M.S. Forward Current	$I_F(\text{RMS})$	11.1	A	
サージ順電流 Surge Forward Current	$I_{FSM}$	120 50Hz正弦全波, 1サイクル, 非くり返し 50Hz Full Sine Wave, 1cycle, Non-repetitive	A	
動作接合温度範囲 Operating Junction Temperature Range	$T_{jw}$	-40~+150	$^\circ\text{C}$	
保存温度範囲 Storage Temperature Range	$T_{stg}$	-40~+150	$^\circ\text{C}$	
締付トルク Mounting torque	$F_{tor}$	推奨値 Recommended Value	0.5 N·m	

OUTLINE DRAWING(mm)



APPROX. NET WEIGHT:1.9 g

電氣的・熱的特性 Electrical/Thermal Characteristics

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	$I_{RM}$	$T_j=25^\circ\text{C}, V_{RM}=V_{RRM}$ , 一素子あたり Per Diode	—	—	5	mA
ピーク順電圧 Peak Forward Voltage	$V_{FM}$	$T_j=25^\circ\text{C}, I_{FM}=5\text{A}$ , 一素子あたり Per Diode	—	—	0.55	V
熱抵抗 Thermal Resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to Case	—	—	3	$^\circ\text{C}/\text{W}$

定格・特性曲線

FIG.1

順電圧特性  
FORWARD CURRENT VS. VOLTAGE

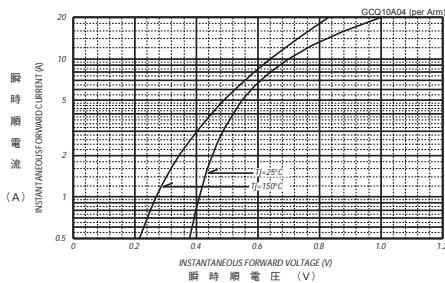


FIG.2

平均順電力損失特性  
AVERAGE FORWARD POWER DISSIPATION

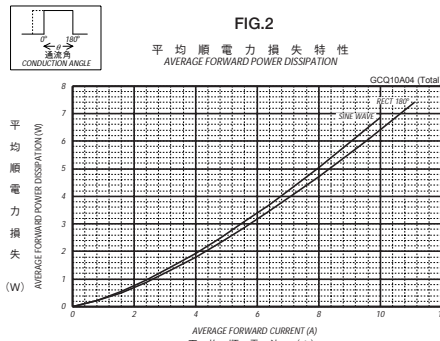


FIG.3

ピーク逆電流 - ピーク逆電圧特性  
PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

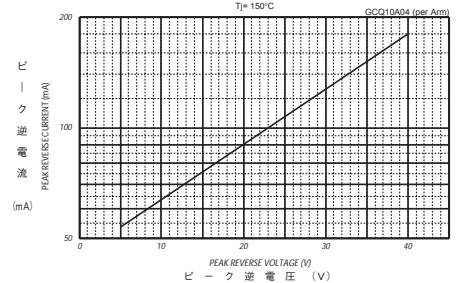


FIG.4

平均逆電力損失  
AVERAGE REVERSE POWER DISSIPATION

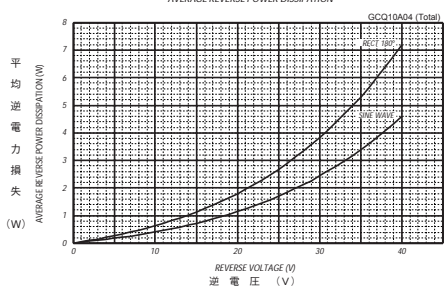


FIG.5

平均順電流 - ケース温度定格  
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

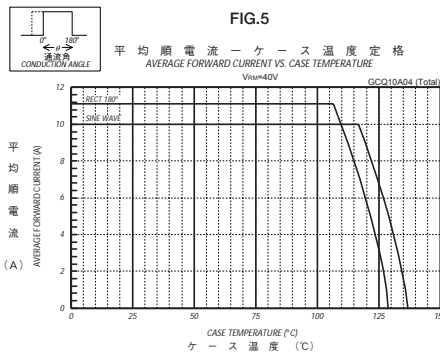


FIG.6

サージ順電流定格  
SURGE CURRENT RATINGS

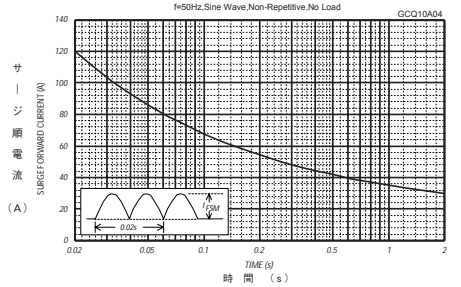


FIG.7

接合容量特性  
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

